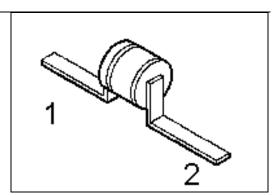


HiRel Silicon Schottky Diode

- HiRel Discrete and Microwave Semiconductor
- General-purpose diodes for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detecting and mixing
- Hermetically sealed microwave package

ESA/SCC Detail Spec. No.: 5512/020

Type Variant No. 03



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Туре	Marking	Ordering Code	Pin Configuration	Package
BAS40-T1 (ql)	-	see below	1 — 2	T1

(ql) Quality Level: P: Professional Quality

H: High Rel Quality

S: Space Quality

ES: ESA Space Quality

(see order instructions for ordering example)



Ма	vim	um	Rati	nae
IVI	ıxım	um	Rati	nas

Parameter	Symbol	Values	Unit
Reverse Voltage	V _R	40	V
Forward Current	I _F	120	mA
Surge Forward Current 1)	I _{FSM}	170	mA
Power Dissipation 2)	P _{tot}	250	mW
Operating Temperature Range	T _{op}	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Soldering Temperature 3)	T _{sol}	+250	°C
Junction Temperature	T _j	150	°C
Thermal Resistance Junction-Case	R _{th(j-c)}	100	K/W

Electrical Characteristics

at T_A =25°C; unless otherwise specified

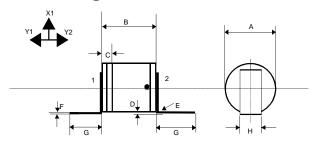
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse Current 1, V _R =40V	I _{R1}	-	-	10	μΑ
Reverse Current 2, V _R =30V	I _{R2}	-	-	1	μΑ
Forward Voltage 1, I _{F1} =1mA	V _{F1}	0,29	0,33	0,39	V
Forward Voltage 2, I _{F2} =10mA	V_{F2}	0,42	0,45	0,54	V
Forward Voltage 3, I _{F3} =40mA	V _{F3}	0,68	0,7	0,85	V
Differential Forward Resistance 4)	R _{FD}	7,5	10	11,5	Ω
IF=10mA, IF=15mA					
AC Characteristics					
Total Capacitance	C _T	2,2	2,9	5,0	pF
V _R =0V; f=1MHz					

Notes.:

- 1.) $t \le 10 \text{ms}$, Duty Cycle=10% 2.) At $T_{\text{CASE}} = 125$ °C. For $T_{\text{CASE}} > 125$ °C derating is required. 3.) During 5 sec. maximum. The same terminal shall not be resoldered until 3 minutes have elapsed.



T1 Package



Symbol	Millimetre		
	min	max	
Α	1,30	1,45	
В	1,15	1,35	
С	ı	0,40	
D	0,10	0,50	
Е	1	0,30	
F	0,06	0,10	
G	5,50	-	
Н	0,40	0,60	

Edition 2011-02
Published by
Infineon Technologies AG
85579 Neubiberg, Germany
© Infineon Technologies AG 2011
All Rights Reserved.

Attention please!

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of an third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.